

Fig. 1

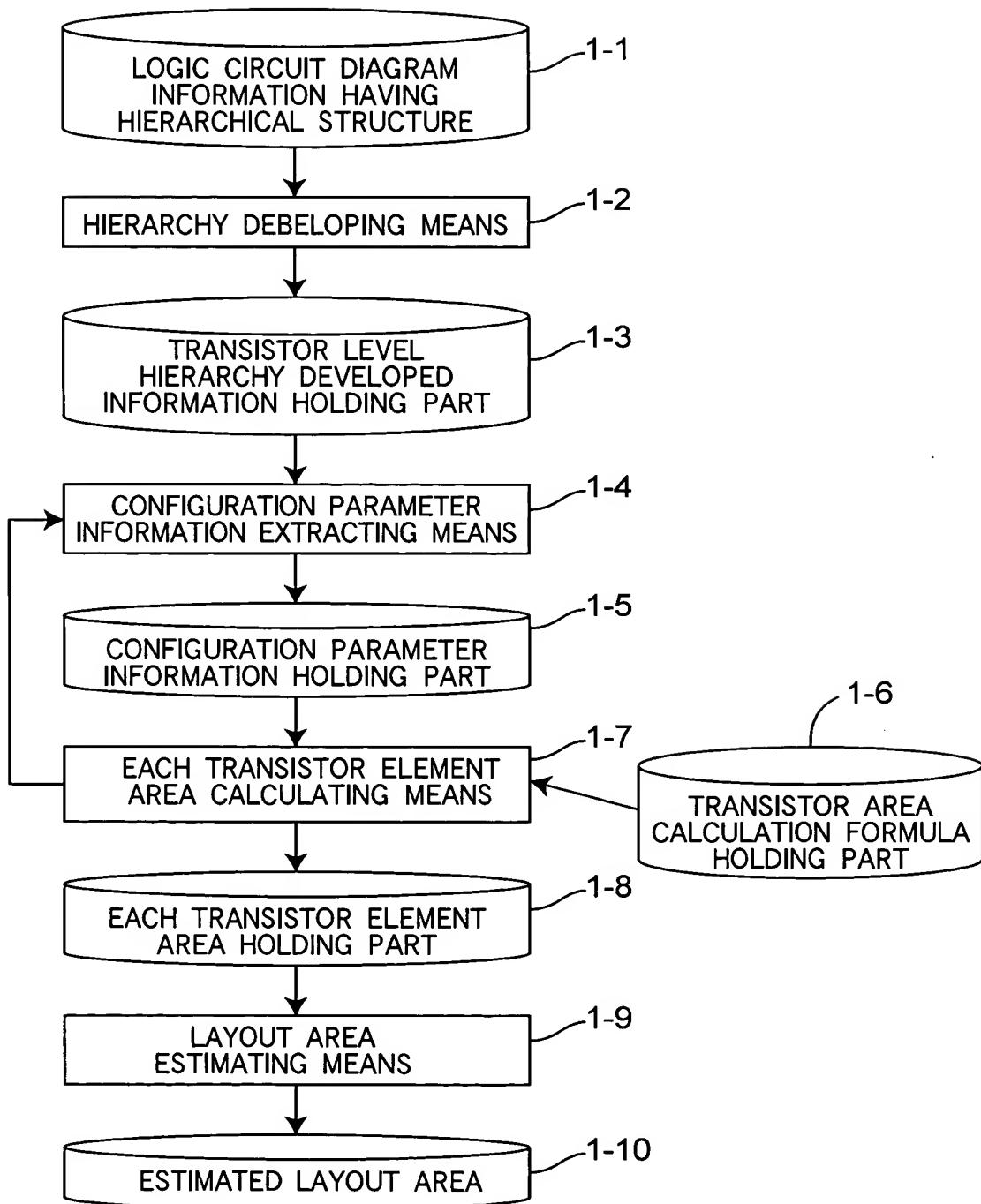


Fig.2

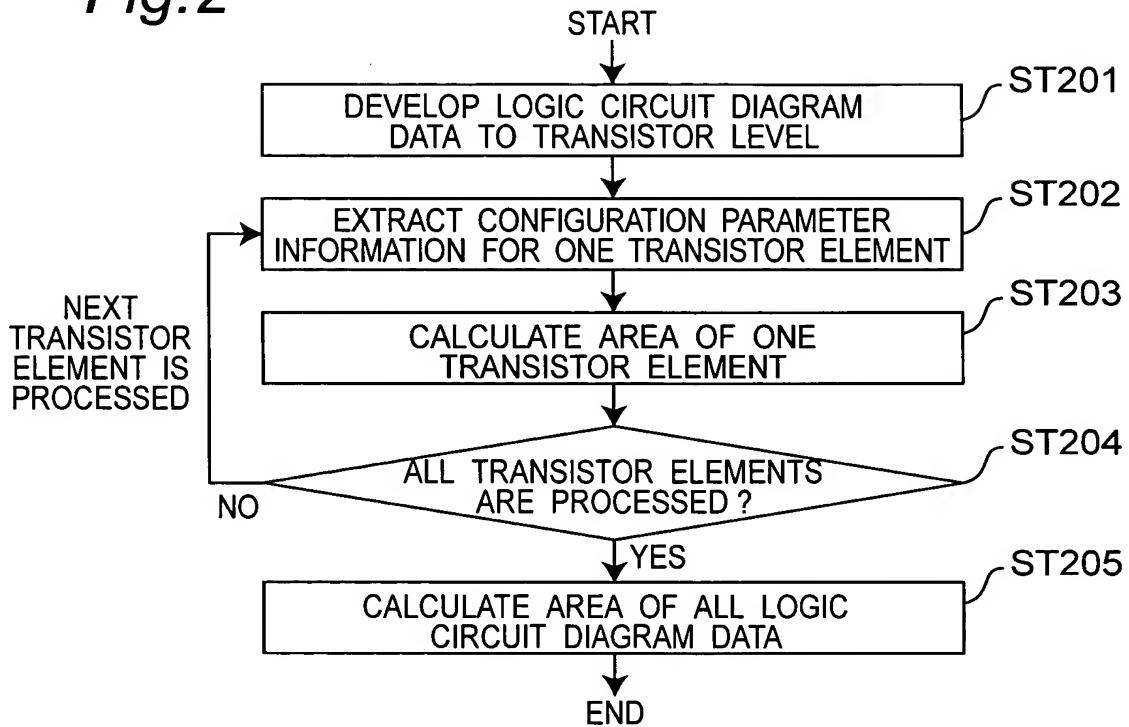


Fig.3

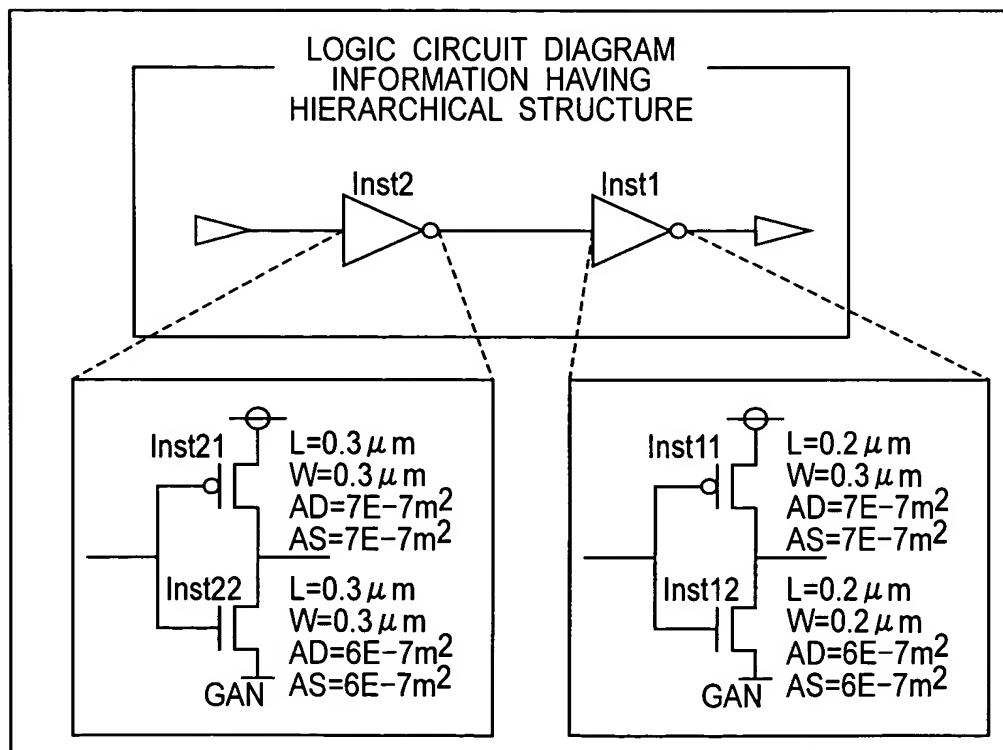


Fig.4

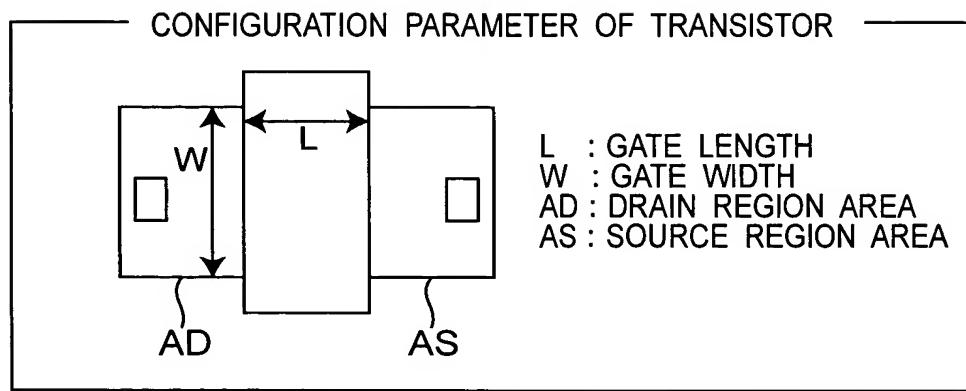


Fig.5

TRANSISTOR AREA CALCULATION
FORMULA HOLDING PART

$$\text{ONE TRANSISTOR AREA} = L \times W + AD + AS$$

Fig.6

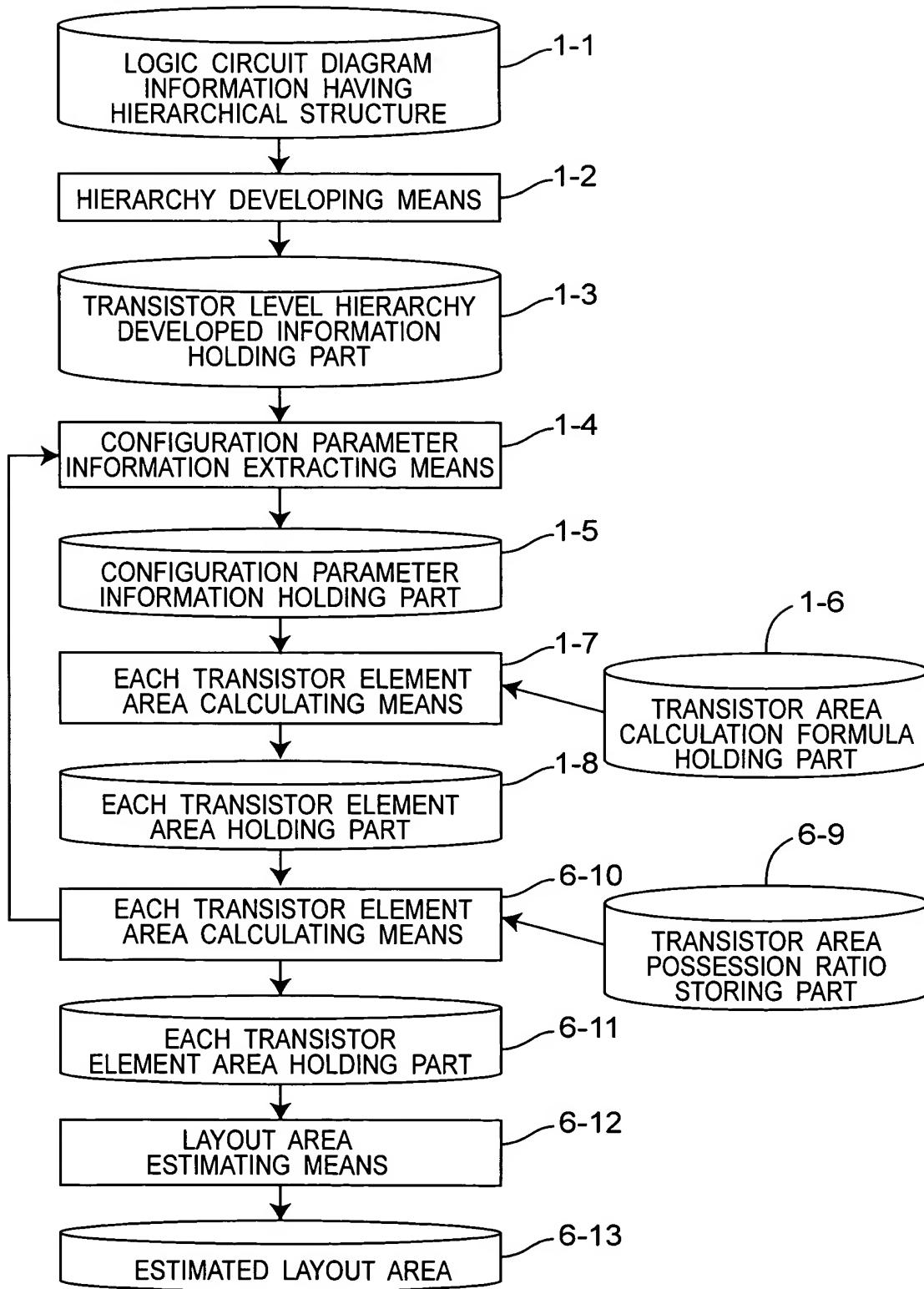


Fig. 7

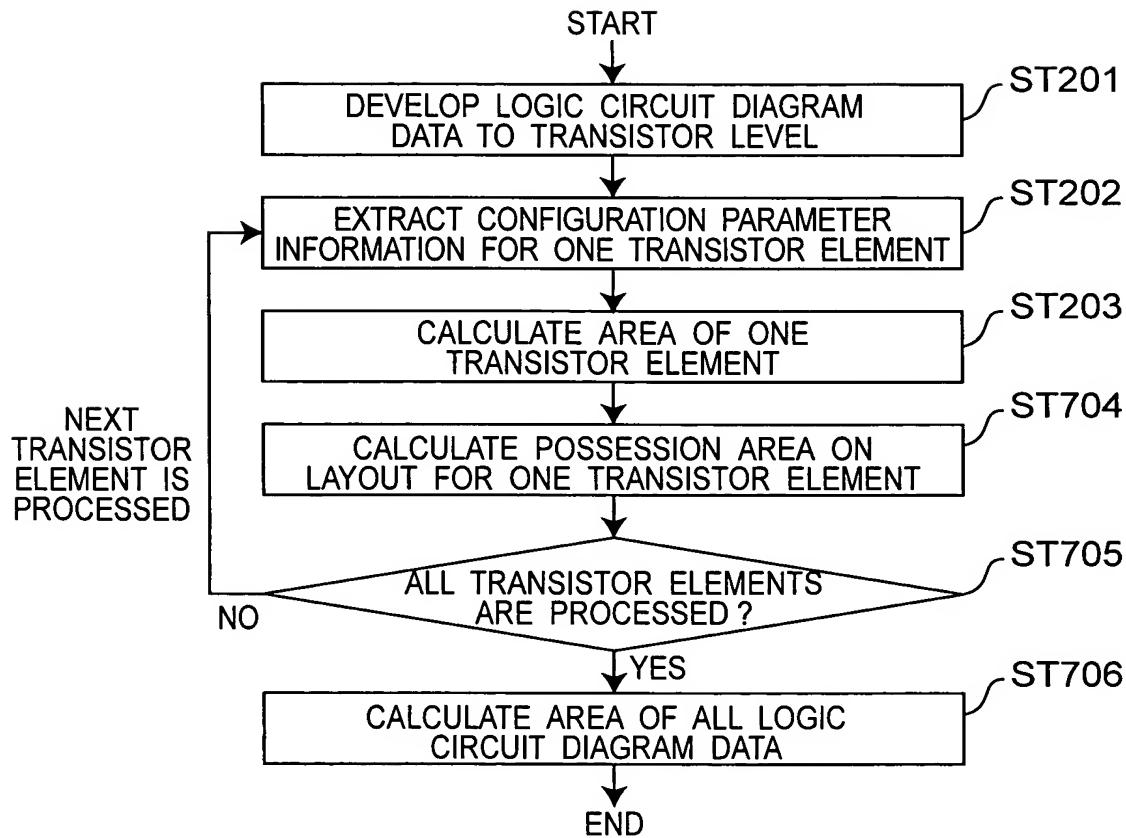


Fig. 8

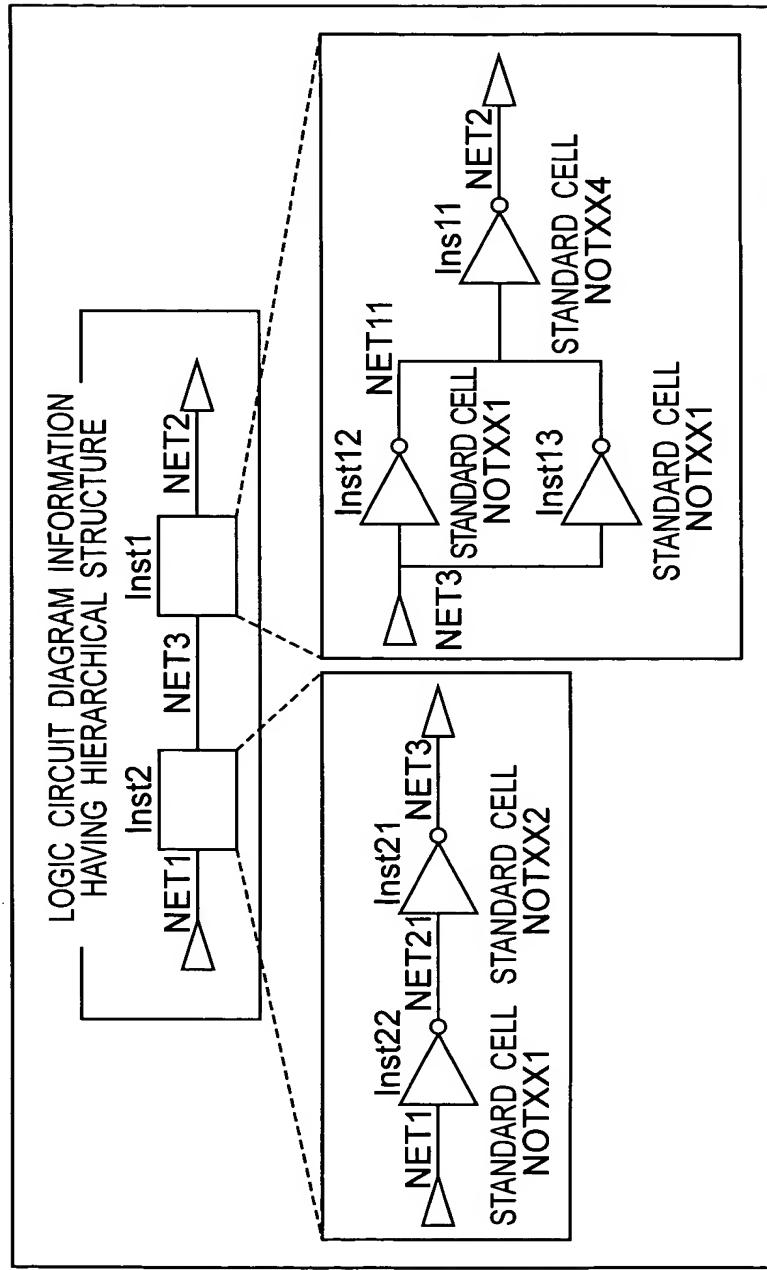


Fig.9

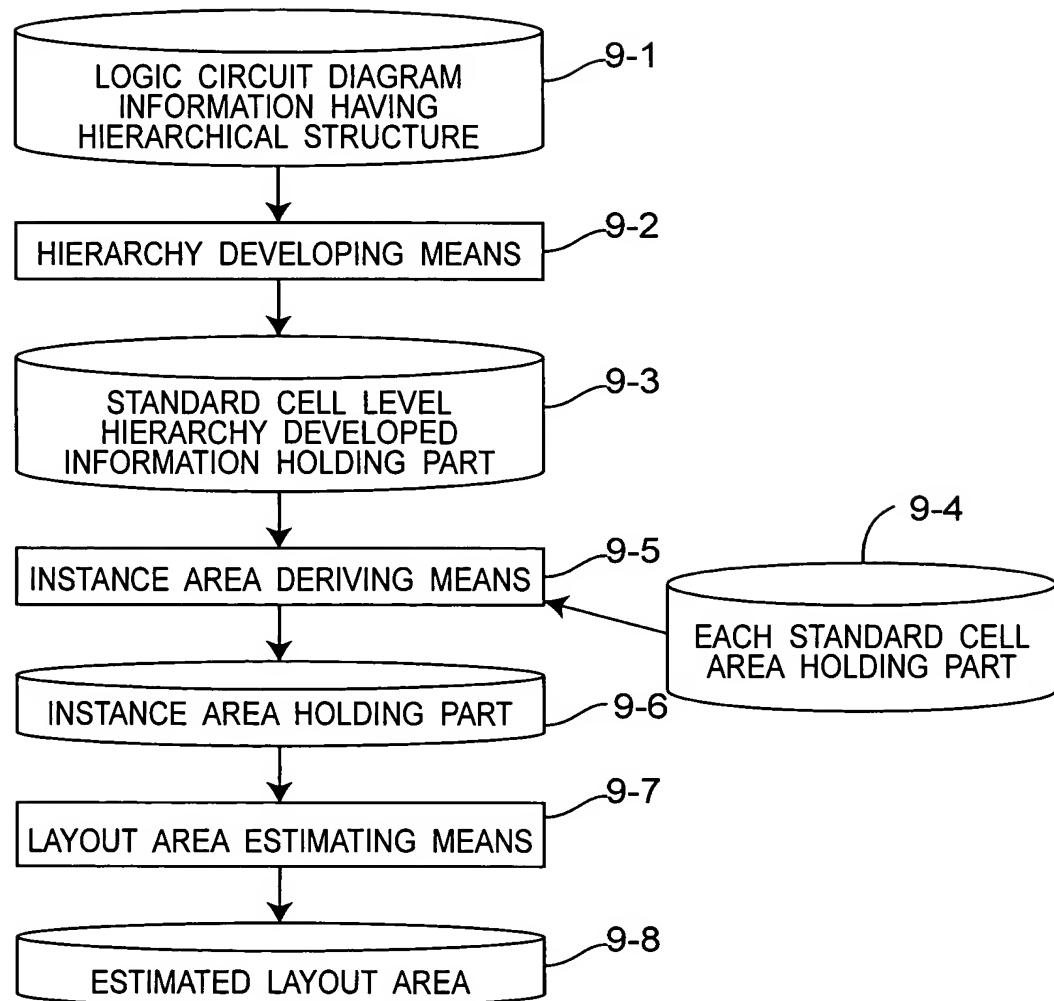


Fig. 10

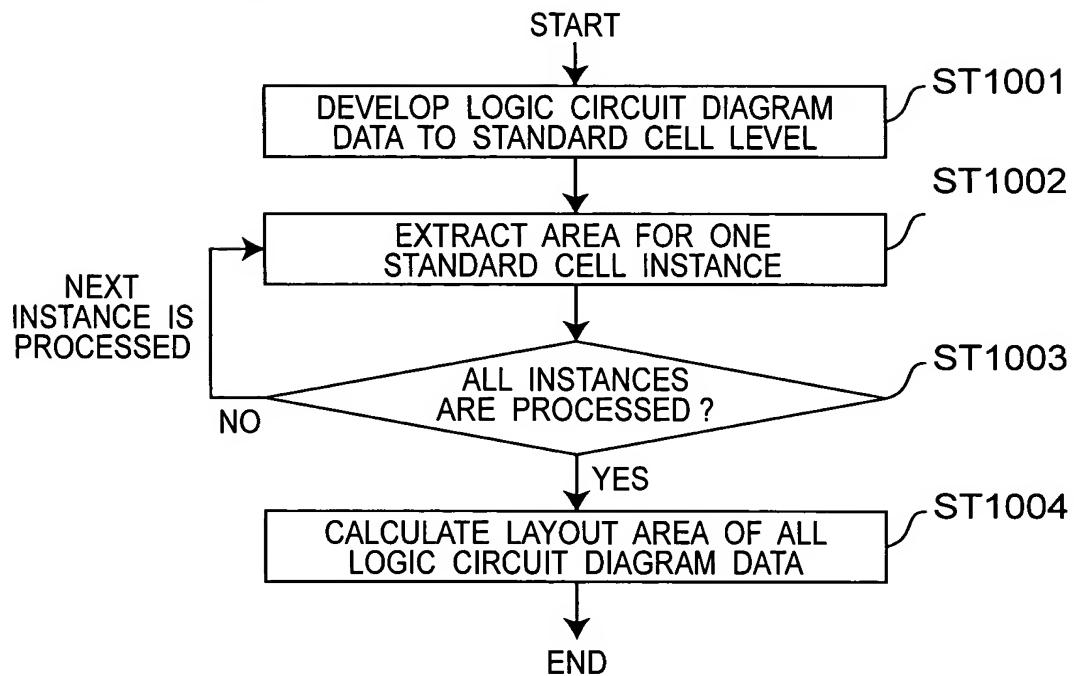


Fig. 11

DEFINITION EXAMPLE OF EACH STANDARD CELL AREA HOLDING PART

NOTXX1	10E-8 μm^2
NOTXX2	20E-8 μm^2
NOTXX4	40E-8 μm^2
NOTXX8	80E-8 μm^2
:	:
:	:

Fig. 12

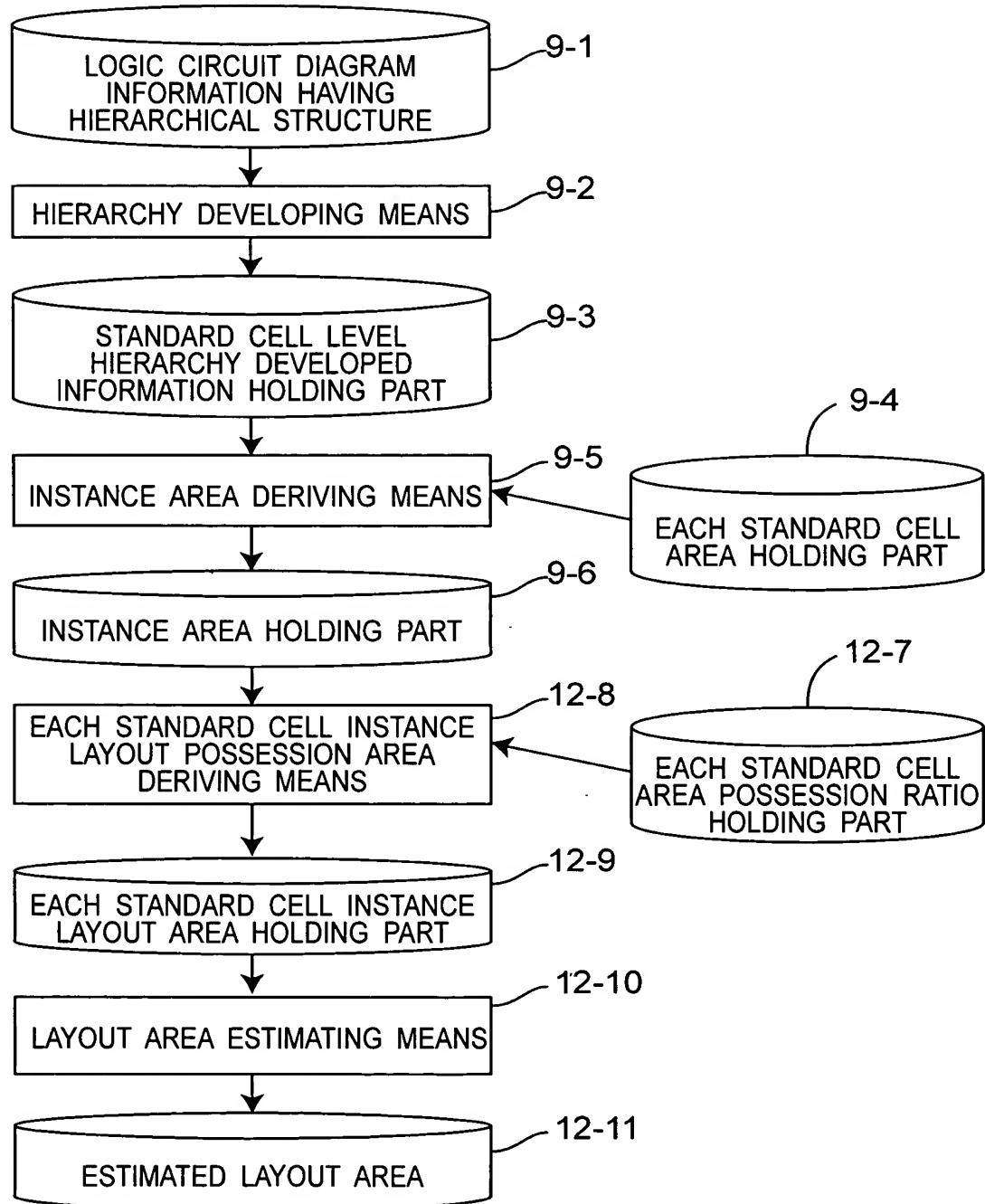


Fig. 13

DEFINITION EXAMPLE OF EACH STANDARD CELL AREA POSSESSION RATIO HOLDING PART

NOTXX1	0.8
NOTXX2	0.9
NOTXX4	0.9
NOTXX8	0.8
:	:
:	:

Fig. 14

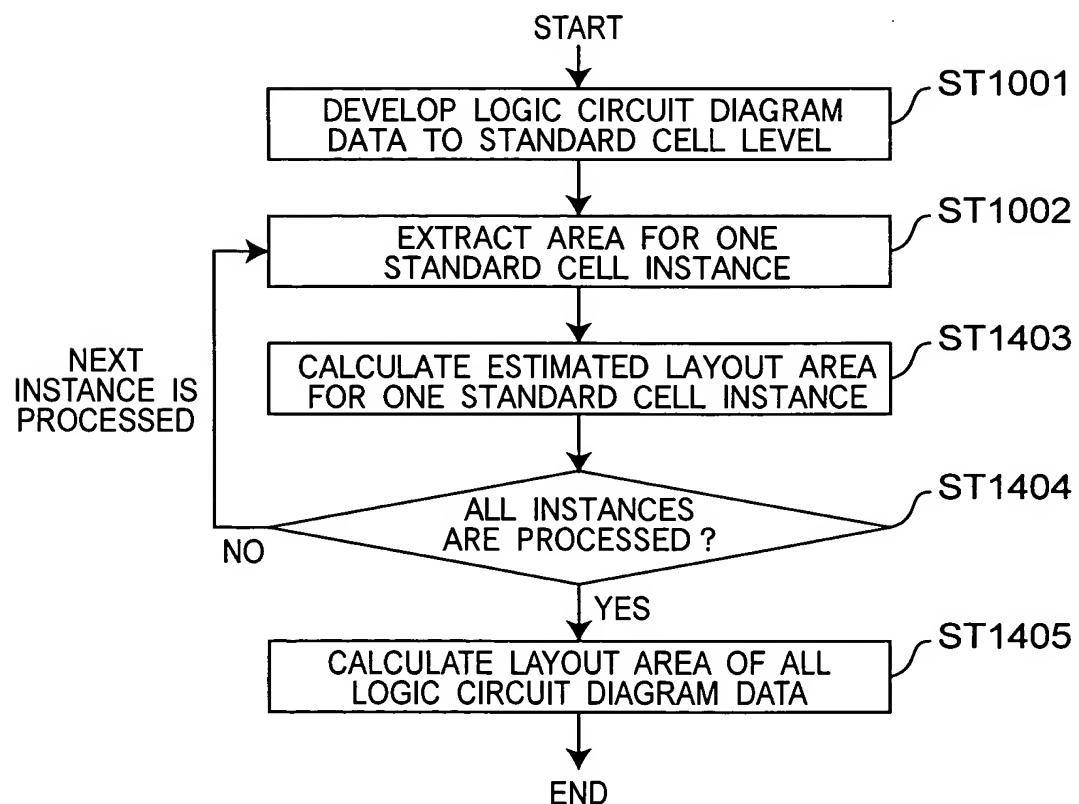


Fig. 15

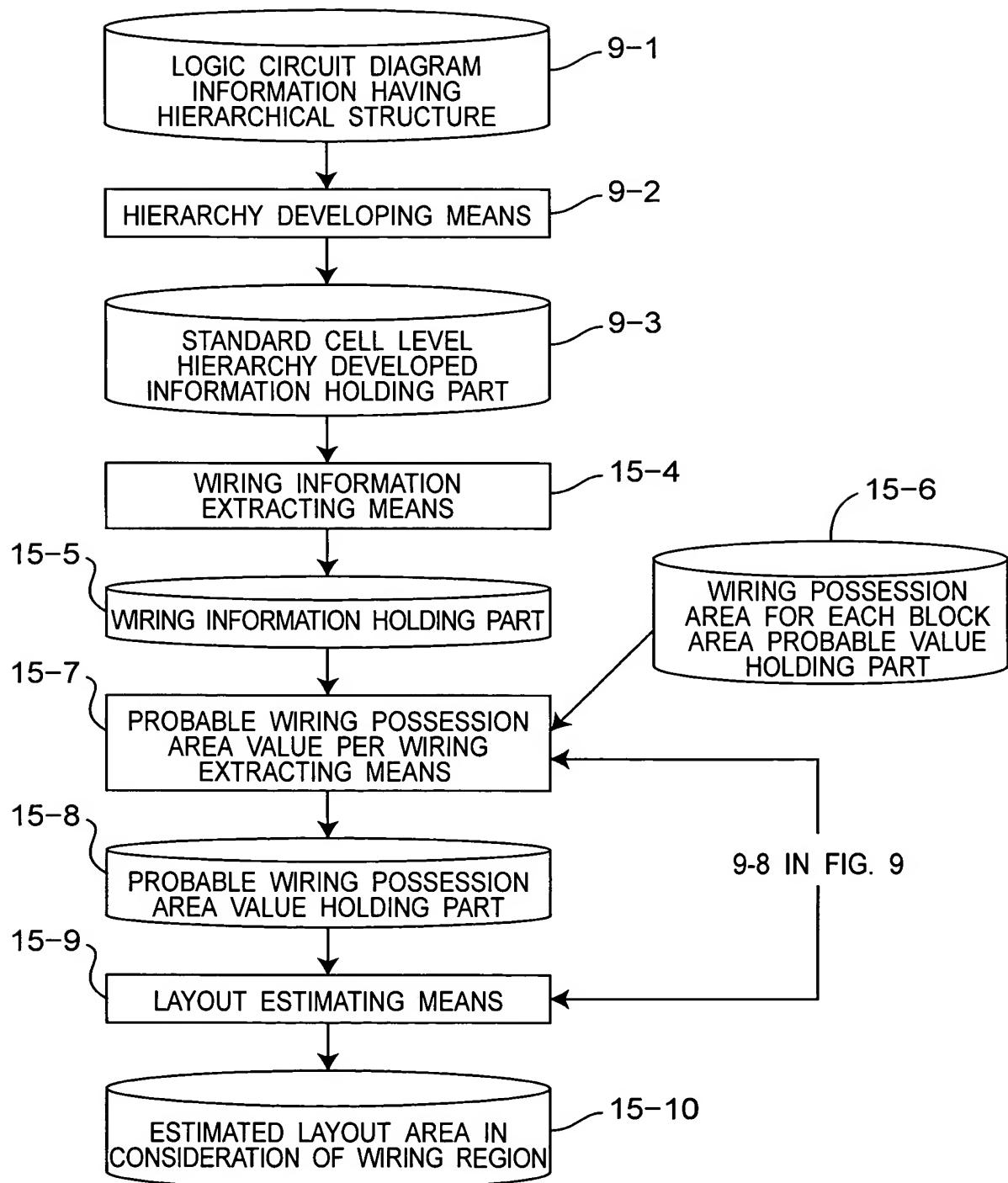


Fig. 16

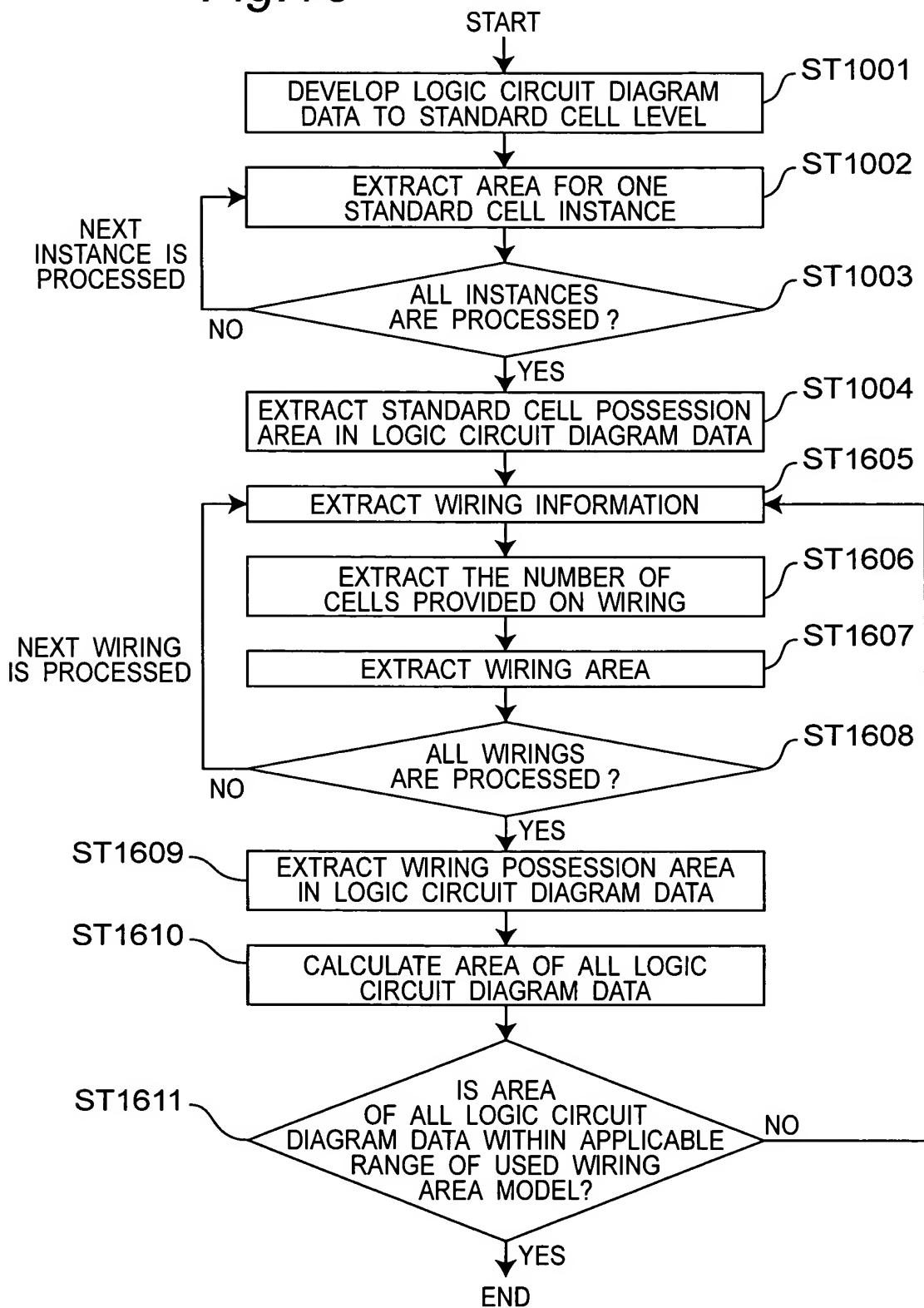


Fig.17

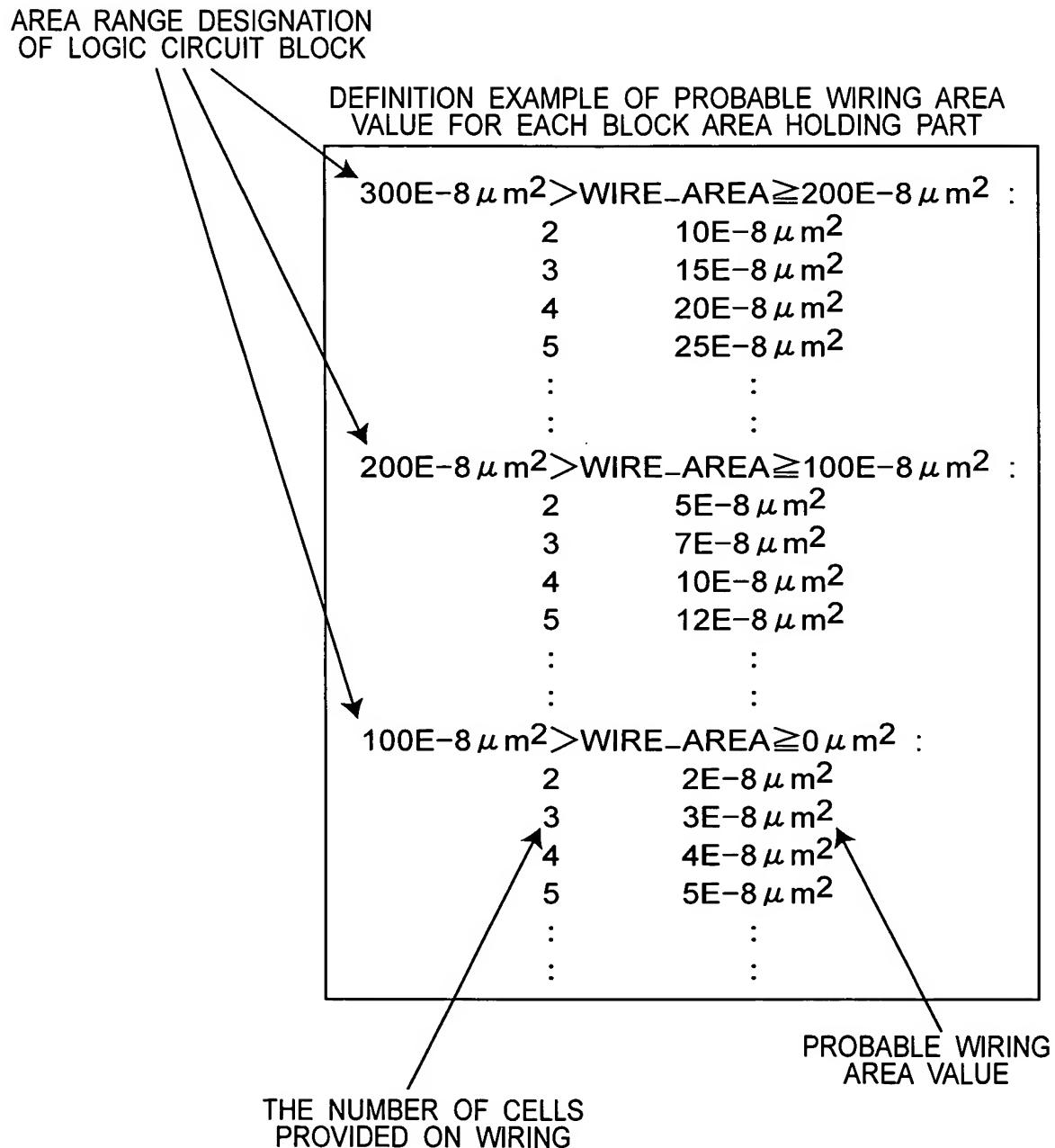


Fig. 18

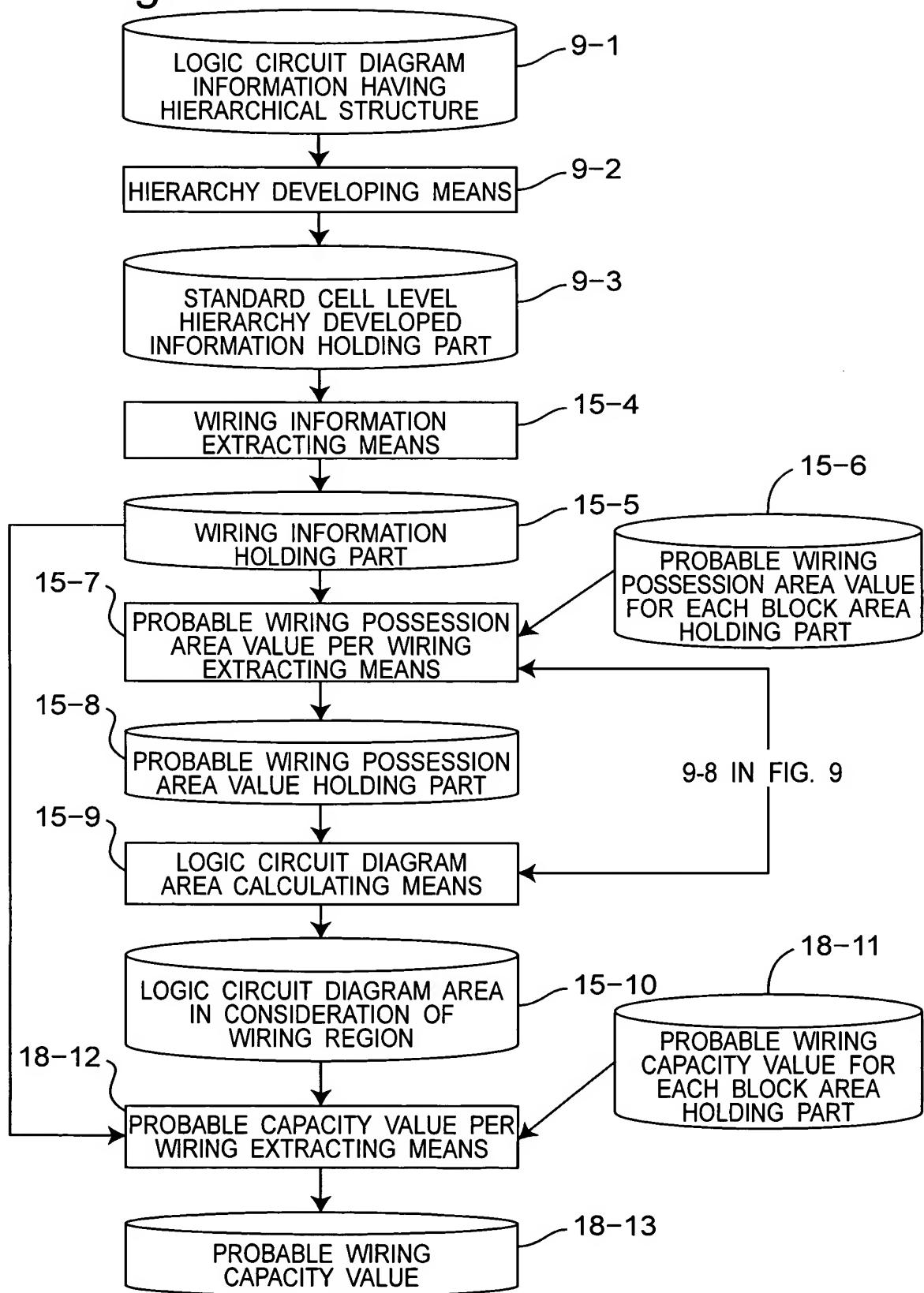


Fig. 19

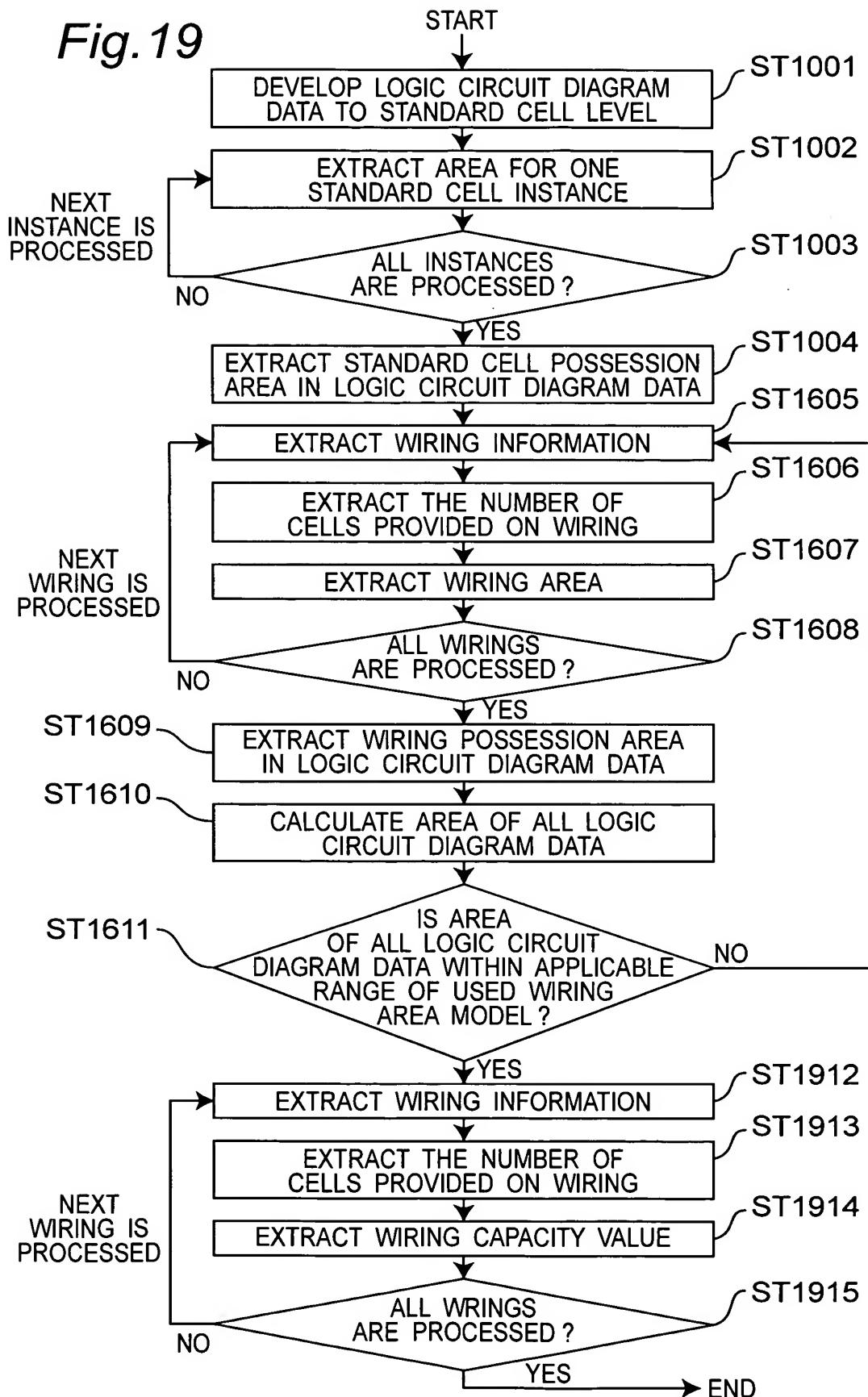


Fig.20

AREA RANGE DESIGNATION
OF LOGIC CIRCUIT BLOCK

DEFINITION EXAMPLE OF PROBABLE WIRING CAPACITY
VALUE FOR EACH BLOCK AREA HOLDING PART

$300E-8 \mu m^2 > WIRE_AREA \geq 200E-8 \mu m^2 :$

2	0.10pf
3	0.13pf
4	0.15pf
5	0.17pf
:	:
:	:

$200E-8 \mu m^2 > WIRE_AREA \geq 100E-8 \mu m^2 :$

2	0.07pf
3	0.08pf
4	0.10pf
5	0.12pf
:	:
:	:

$100E-8 \mu m^2 > WIRE_AREA \geq 0 \mu m^2 :$

2	0.03pf
3	0.04pf
4	0.05pf
5	0.06pf
:	:
:	:

THE NUMBER OF CELLS
PROVIDED ON WIRING

PROBABLE WIRING
AREA VALUE

Fig.21

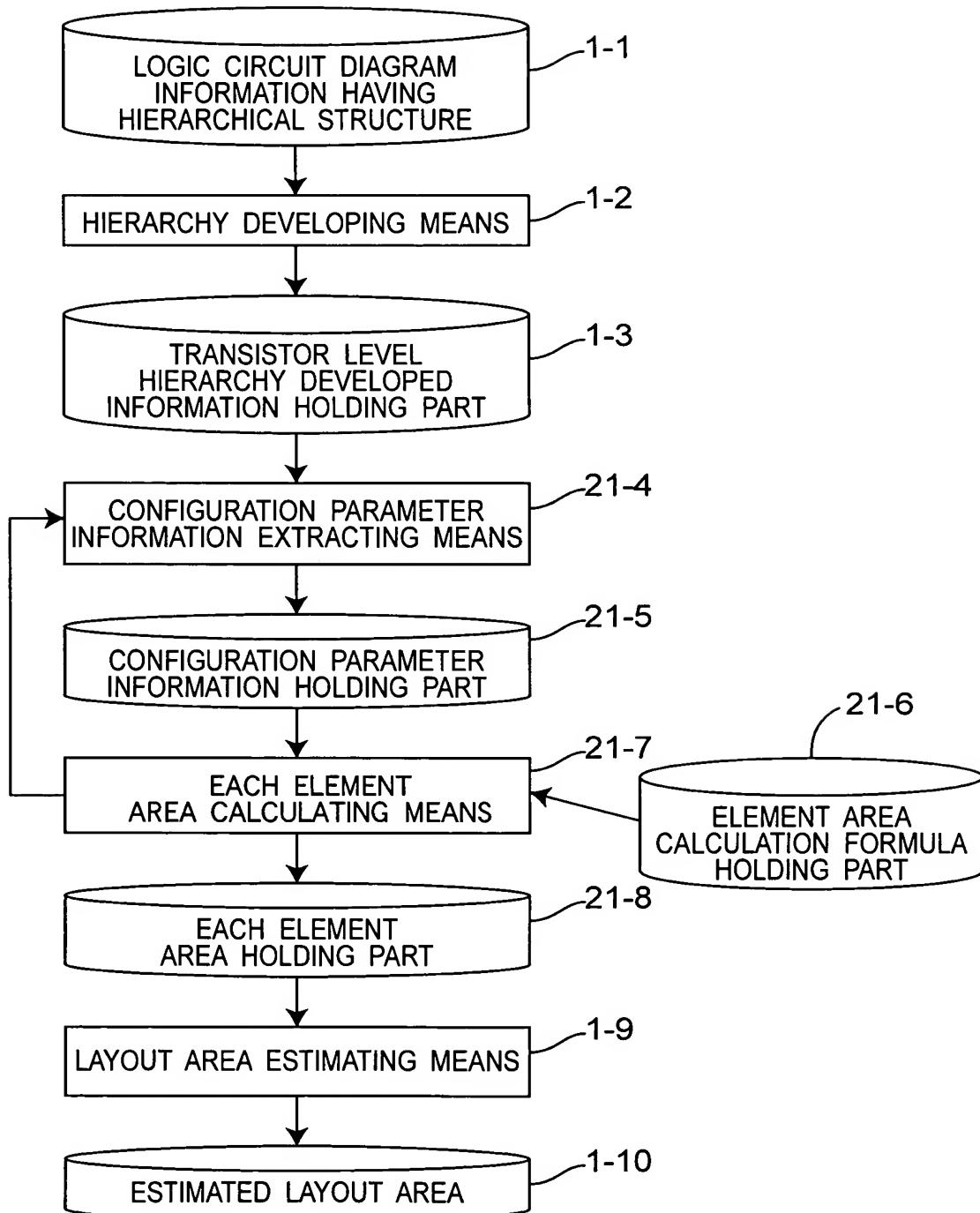


Fig.22

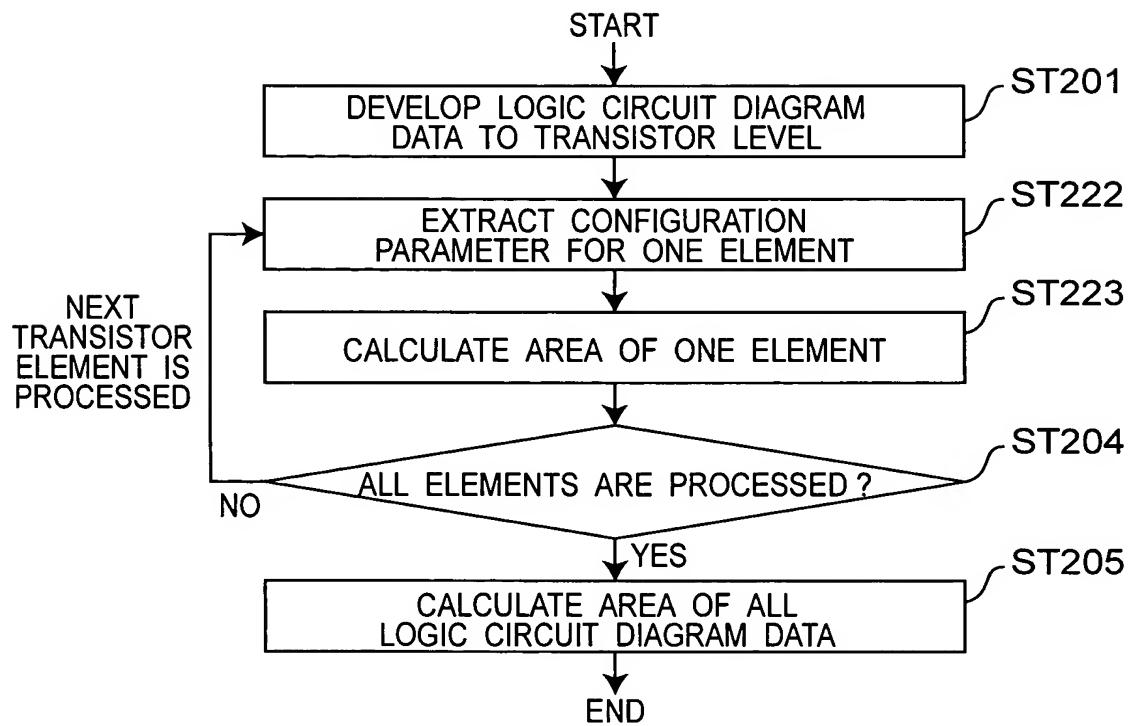
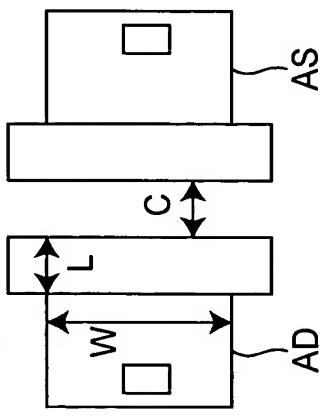


Fig.23

CONFIGURATION PARAMETER OF TRANSISTOR



PARAMETER OF RESISTANCE : RESISTANCE VALUE

PARAMETER OF CAPACITY : CAPACITY VALUE

Fig.24

TRANSISTOR AREA CALCULATION FORMULA HOLDING PART

ONE TRANSISTOR AREA = $L \times W \times M + AD + AS + D \times W$

AREA OF ONE RESISTANCE = $[RESISTANCE\ VALUE]/[RESISTANCE\ VALUE\ PER\ UNIT\ LENGTH] \times [WIRING\ WIDTH]$

AREA OF ONE CAPACITY = $[CAPACITY\ VALUE]/[CAPACITY\ VALUE\ PER\ UNIT\ LENGTH] \times [WIRING\ WIDTH]$

Fig. 25

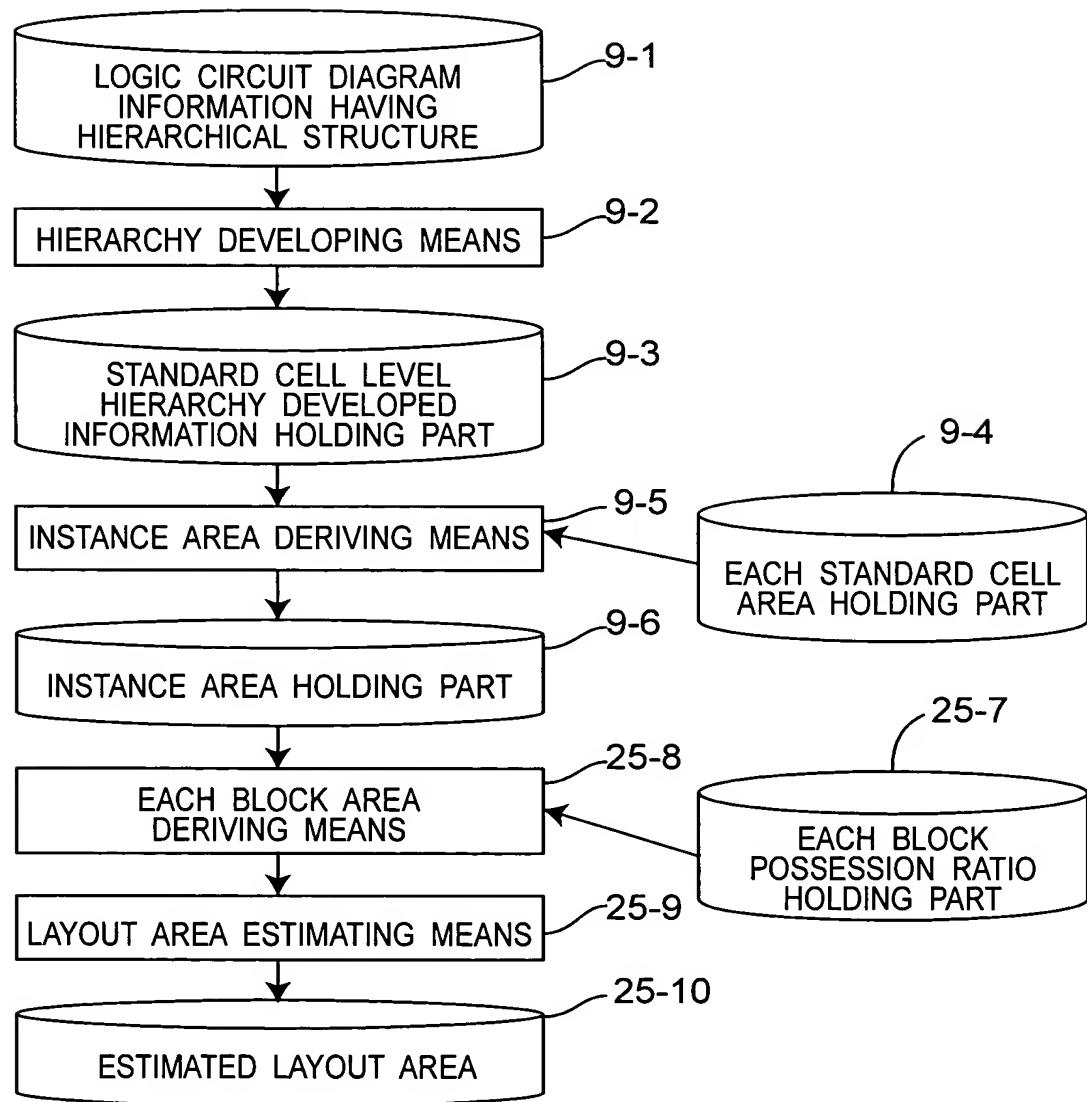


Fig.26

